

Shoji Ikeda

List of Publications by Year in descending order

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129
papers

11,327
citations

76326

40
h-index

30087

103
g-index

129
all docs

129
docs citations

129
times ranked

5412
citing authors

#	ARTICLE	IF	CITATIONS
1	A perpendicular-anisotropy CoFeB/MgO magnetic tunnel junction. Nature Materials, 2010, 9, 721-724.	27.5	3,020
2	Tunnel magnetoresistance of 604% at 300K by suppression of Ta diffusion in CoFeB/MgO/CoFeB pseudo-spin-valves annealed at high temperature. Applied Physics Letters, 2008, 93, .	3.3	1,259
3	Magnetic Tunnel Junctions for Spintronic Memories and Beyond. IEEE Transactions on Electron Devices, 2007, 54, 991-1002.	3.0	460
4	Electric-field effects on thickness dependent magnetic anisotropy of sputtered MgO/Co ₄₀ Fe ₄₀ B ₂₀ /Ta structures. Applied Physics Letters, 2010, 96, .	3.3	443
5	Electric field-induced magnetization reversal in a perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction. Applied Physics Letters, 2012, 101, .	3.3	341
6	Fabrication of a Nonvolatile Full Adder Based on Logic-in-Memory Architecture Using Magnetic Tunnel Junctions. Applied Physics Express, 0, 1, 091301.	2.4	302
7	Effect of electrode composition on the tunnel magnetoresistance of pseudo-spin-valve magnetic tunnel junction with a MgO tunnel barrier. Applied Physics Letters, 2007, 90, 212507.	3.3	293
8	Perpendicular-anisotropy CoFeB-MgO magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure. Applied Physics Letters, 2012, 101, .	3.3	255
9	Dependence of Giant Tunnel Magnetoresistance of Sputtered CoFeB/MgO/CoFeB Magnetic Tunnel Junctions on MgO Barrier Thickness and Annealing Temperature. Japanese Journal of Applied Physics, 2005, 44, L587-L589.	1.5	242
10	Properties of magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure down to junction diameter of 11 nm. Applied Physics Letters, 2014, 105, .	3.3	240
11	2 Mb SPRAM (Spin-Transfer Torque RAM) With Bit-by-Bit Bi-Directional Current Write and Parallelizing-Direction Current Read. IEEE Journal of Solid-State Circuits, 2008, 43, 109-120.	5.4	212
12	Effect of high annealing temperature on giant tunnel magnetoresistance ratio of CoFeB/MgO/CoFeB magnetic tunnel junctions. Applied Physics Letters, 2006, 89, 232510.	3.3	205
13	Current-Driven Magnetization Switching in CoFeB/MgO/CoFeB Magnetic Tunnel Junctions. Japanese Journal of Applied Physics, 2005, 44, L1267.	1.5	182
14	Giant tunnel magnetoresistance and high annealing stability in CoFeB/MgO/CoFeB magnetic tunnel junctions with synthetic pinned layer. Applied Physics Letters, 2006, 89, 042506.	3.3	150
15	Junction size effect on switching current and thermal stability in CoFeB/MgO perpendicular magnetic tunnel junctions. Applied Physics Letters, 2011, 99, .	3.3	143
16	Current-induced domain wall motion in perpendicularly magnetized CoFeB nanowire. Applied Physics Letters, 2011, 98, .	3.3	135
17	Current-induced effective field in perpendicularly magnetized Ta/CoFeB/MgO wire. Applied Physics Letters, 2011, 98, .	3.3	133
18	MgO barrier-perpendicular magnetic tunnel junctions with CoFe/Pd multilayers and ferromagnetic insertion layers. Applied Physics Letters, 2009, 95, .	3.3	130

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19	Current-Induced Magnetization Switching in MgO Barrier Based Magnetic Tunnel Junctions with CoFeB/Ru/CoFeB Synthetic Ferrimagnetic Free Layer. Japanese Journal of Applied Physics, 2006, 45, L1057-L1060.	1.5	125
20	Domain Structure in CoFeB Thin Films With Perpendicular Magnetic Anisotropy. IEEE Magnetics Letters, 2011, 2, 3000304-3000304.	1.1	124
21	An Overview of Nonvolatile Emerging Memoriesâ€™ Spintronics for Working Memories. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2016, 6, 109-119.	3.6	121
22	MgO/CoFeB/Ta/CoFeB/MgO Recording Structure in Magnetic Tunnel Junctions With Perpendicular Easy Axis. IEEE Transactions on Magnetics, 2013, 49, 4437-4440.	2.1	120
23	Enhanced interface perpendicular magnetic anisotropy in Ta CoFeB MgO using nitrogen doped Ta underlayers. Applied Physics Letters, 2013, 102, .	3.3	117
24	A 32-Mb SPRAM With 2T1R Memory Cell, Localized Bi-Directional Write Driver and '1'/'0' Dual-Array Equalized Reference Scheme. IEEE Journal of Solid-State Circuits, 2010, 45, 869-879.	5.4	115
25	Dependence of magnetic anisotropy on MgO thickness and buffer layer in Co ₂₀ Fe ₆₀ B ₂₀ -MgO structure. Journal of Applied Physics, 2011, 109, .	2.5	109
26	Standby-Power-Free Integrated Circuits Using MTJ-Based VLSI Computing. Proceedings of the IEEE, 2016, 104, 1844-1863.	21.3	102
27	Dependence of Tunnel Magnetoresistance in MgO Based Magnetic Tunnel Junctions on Ar Pressure during MgO Sputtering. Japanese Journal of Applied Physics, 2005, 44, L1442-L1445.	1.5	99
28	Three terminal magnetic tunnel junction utilizing the spin Hall effect of iridium-doped copper. Applied Physics Letters, 2013, 102, .	3.3	99
29	Magnetization switching in a CoFeB/MgO magnetic tunnel junction by combining spin-transfer torque and electric field-effect. Applied Physics Letters, 2014, 104, .	3.3	87
30	Atomic-Scale Structure and Local Chemistry of CoFeBâ€™MgO Magnetic Tunnel Junctions. Nano Letters, 2016, 16, 1530-1536.	9.1	85
31	Current-Induced Magnetization Switching in MgO Barrier Magnetic Tunnel Junctions With CoFeB-Based Synthetic Ferrimagnetic Free Layers. IEEE Transactions on Magnetics, 2008, 44, 1962-1967.	2.1	83
32	Standby-Power-Free Compact Ternary Content-Addressable Memory Cell Chip Using Magnetic Tunnel Junction Devices. Applied Physics Express, 0, 2, 023004.	2.4	73
33	A 1 Mb Nonvolatile Embedded Memory Using 4T2MTJ Cell With 32 b Fine-Grained Power Gating Scheme. IEEE Journal of Solid-State Circuits, 2013, 48, 1511-1520.	5.4	70
34	Magnetic tunnel junction for nonvolatile CMOS logic. , 2010, , .		66
35	Observation of boron diffusion in an annealed Ta/CoFeB/MgO magnetic tunnel junction with standing-wave hard x-ray photoemission. Applied Physics Letters, 2012, 101, .	3.3	64
36	RECENT PROGRESS OF PERPENDICULAR ANISOTROPY MAGNETIC TUNNEL JUNCTIONS FOR NONVOLATILE VLSI. Spin, 2012, 02, 1240003.	1.3	63

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37	A nondestructive analysis of the B diffusion in Ta/CoFeB/MgO/CoFeB/Ta magnetic tunnel junctions by hard x-ray photoemission. Applied Physics Letters, 2010, 96, .	3.3	60
38	Origin of the collapse of tunnel magnetoresistance at high annealing temperature in CoFeB/MgO perpendicular magnetic tunnel junctions. Applied Physics Letters, 2011, 99, .	3.3	55
39	In-plane magnetic field dependence of electric field-induced magnetization switching. Applied Physics Letters, 2013, 103, .	3.3	53
40	Nonvolatile Logic-in-Memory LSI Using Cycle-Based Power Gating and its Application to Motion-Vector Prediction. IEEE Journal of Solid-State Circuits, 2015, 50, 476-489.	5.4	53
41	Transmission electron microscopy study on the effect of various capping layers on CoFeB/MgO/CoFeB pseudo spin valves annealed at different temperatures. Journal of Applied Physics, 2012, 111, .	2.5	50
42	Tunnel magnetoresistance properties and film structures of double MgO barrier magnetic tunnel junctions. Applied Physics Letters, 2010, 96, .	3.3	49
43	Comprehensive study of CoFeB-MgO magnetic tunnel junction characteristics with single- and double-interface scaling down to 1X nm. , 2013, , .		49
44	Pd Layer Thickness Dependence of Tunnel Magnetoresistance Properties in CoFeB/MgO-Based Magnetic Tunnel Junctions with Perpendicular Anisotropy CoFe/Pd Multilayers. Applied Physics Express, 2011, 4, 023002.	2.4	48
45	20-nm magnetic domain wall motion memory with ultralow-power operation. , 2013, , .		42
46	Nonvolatile logic-in-memory array processor in 90nm MTJ/MOS achieving 75% leakage reduction using cycle-based power gating. , 2013, , .		41
47	A 47.14- μm^2 200-MHz MOS/MTJ-Hybrid Nonvolatile Microcontroller Unit Embedding STT-MRAM and FPGA for IoT Applications. IEEE Journal of Solid-State Circuits, 2019, 54, 2991-3004.	5.4	39
48	Influence of Heavy Ion Irradiation on Perpendicular-Anisotropy CoFeB-MgO Magnetic Tunnel Junctions. IEEE Transactions on Nuclear Science, 2014, 61, 1710-1716.	2.0	35
49	Atomic structure and electronic properties of MgO grain boundaries in tunnelling magnetoresistive devices. Scientific Reports, 2017, 7, 45594.	3.3	35
50	Co/Pt multilayer based reference layers in magnetic tunnel junctions for nonvolatile spintronics VLSIs. Japanese Journal of Applied Physics, 2014, 53, 04EM02.	1.5	33
51	14ns write speed 128Mb density Embedded STT-MRAM with endurance $>10^{10}$ and 10yrs retention@85°C using novel low damage MTJ integration process. , 2018, , .		33
52	Magnetotransport measurements of current induced effective fields in Ta/CoFeB/MgO. Applied Physics Letters, 2013, 103, .	3.3	30
53	Magnetization reversal induced by in-plane current in Ta/CoFeB/MgO structures with perpendicular magnetic easy axis. Journal of Applied Physics, 2014, 115, 17C714.	2.5	30
54	Dependence of Magnetic Anisotropy in Co ₂₀ Fe ₆₀ B ₂₀ Free Layers on Capping Layers in MgO-Based Magnetic Tunnel Junctions with In-Plane Easy Axis. Applied Physics Express, 2012, 5, 053002.	2.4	28

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55	Magnetic properties of MgO-[Co/Pt] multilayers with a CoFeB insertion layer. Journal of Applied Physics, 2013, 113, .	2.5	28
56	Effects of boron composition on tunneling magnetoresistance ratio and microstructure of CoFeB/MgO/CoFeB pseudo-spin-valve magnetic tunnel junctions. Journal of Applied Physics, 2012, 111, 043913.	2.5	27
57	Scalability of Quad Interface p-MTJ for 1X nm STT-MRAM With 10-ns Low Power Write Operation, 10 Years Retention and Endurance > 10 ¹¹ . IEEE Transactions on Electron Devices, 2020, 67, 5368-5373.	3.0	26
58	Dual-Port SOT-MRAM Achieving 90-MHz Read and 60-MHz Write Operations Under Field-Assistance-Free Condition. IEEE Journal of Solid-State Circuits, 2021, 56, 1116-1128.	5.4	24
59	Co/Pt multilayer-based magnetic tunnel junctions with a CoFeB/Ta insertion layer. Journal of Applied Physics, 2014, 115, 17C719.	2.5	22
60	Novel Quad interface MTJ technology and its first demonstration with high thermal stability and switching efficiency for STT-MRAM beyond 2Xnm. , 2019, , .		22
61	Domain Wall Motion Device for Nonvolatile Memory and Logic â€” Size Dependence of Device Properties. IEEE Transactions on Magnetics, 2014, 50, 1-6.	2.1	21
62	Perpendicular-anisotropy CoFeB-MgO based magnetic tunnel junctions scaling down to 1X nm. , 2014, , .		20
63	Perpendicular Magnetic Tunnel Junctions with CoFe/Pd Multilayer Electrodes and an MgO Barrier. IEEE Transactions on Magnetics, 2009, 45, 3476-3479.	2.1	19
64	Novel Quad-Interface MTJ Technology and its First Demonstration With High Thermal Stability Factor and Switching Efficiency for STT-MRAM Beyond 2X nm. IEEE Transactions on Electron Devices, 2020, 67, 995-1000.	3.0	19
65	Dependence of tunnel magnetoresistance on ferromagnetic electrode materials in MgO-barrier magnetic tunnel junctions. Journal of Magnetism and Magnetic Materials, 2007, 310, 1937-1939.	2.3	18
66	Spin-torque switching window, thermal stability, and material parameters of MgO tunnel junctions. Applied Physics Letters, 2011, 98, 162502.	3.3	18
67	Recent Progresses in STT-MRAM and SOT-MRAM for Next Generation MRAM. , 2020, , .		18
68	Process-induced damage and its recovery for a CoFeBâ€”MgO magnetic tunnel junction with perpendicular magnetic easy axis. Japanese Journal of Applied Physics, 2014, 53, 103001.	1.5	17
69	Improvement of Thermal Tolerance of CoFeBâ€”MgO Perpendicular-Anisotropy Magnetic Tunnel Junctions by Controlling Boron Composition. IEEE Transactions on Magnetics, 2016, 52, 1-4.	2.1	17
70	Impact of Tungsten Sputtering Condition on Magnetic and Transport Properties of Double-MgO Magnetic Tunneling Junction With CoFeB/W/CoFeB Free Layer. IEEE Transactions on Magnetics, 2017, 53, 1-4.	2.1	17
71	Magnetic tunnel junctions with perpendicular easy axis at junction diameter of less than 20 nm. Japanese Journal of Applied Physics, 2017, 56, 0802A6.	1.5	17
72	Soft errors in 10-nm-scale magnetic tunnel junctions exposed to high-energy heavy-ion radiation. Japanese Journal of Applied Physics, 2017, 56, 0802B4.	1.5	17

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73	Tunnel magnetoresistance properties and annealing stability in perpendicular anisotropy MgO-based magnetic tunnel junctions with different stack structures. Journal of Applied Physics, 2011, 109, .	2.5	16
74	Annealing temperature dependence of magnetic properties of CoFeB/MgO stacks on different buffer layers. Japanese Journal of Applied Physics, 2017, 56, 0802B2.	1.5	14
75	Design and Fabrication of a One-Transistor/One-Resistor Nonvolatile Binary Content-Addressable Memory Using Perpendicular Magnetic Tunnel Junction Devices with a Fine-Grained Power-Gating Scheme. Japanese Journal of Applied Physics, 2011, 50, 063004.	1.5	13
76	1T1MTJ STT-MRAM Cell Array Design with an Adaptive Reference Voltage Generator for Improving Device Variation Tolerance. , 2015, , .		13
77	Trend of tunnel magnetoresistance and variation in threshold voltage for keeping data load robustness of metal-oxide-semiconductor/magnetic tunnel junction hybrid latches. Journal of Applied Physics, 2014, 115, 17C728.	2.5	12
78	Insertion Layer Thickness Dependence of Magnetic and Electrical Properties for Double-CoFeB/MgO-Interface Magnetic Tunnel Junctions. IEEE Transactions on Magnetics, 2019, 55, 1-4.	2.1	12
79	Direct measurement of current-induced fieldlike torque in magnetic tunnel junctions. Journal of Applied Physics, 2009, 105, .	2.5	11
80	CoFeB Inserted Perpendicular Magnetic Tunnel Junctions with CoFe/Pd Multilayers for High Tunnel Magnetoresistance Ratio. Japanese Journal of Applied Physics, 2010, 49, 04DM04.	1.5	11
81	Evidence of a reduction reaction of oxidized iron/cobalt by boron atoms diffused toward naturally oxidized surface of CoFeB layer during annealing. Applied Physics Letters, 2015, 106, 142407.	3.3	11
82	Synthetic antiferromagnetic layer based on Pt/Ru/Pt spacer layer with 1.05%nm interlayer exchange oscillation period for spin-orbit torque devices. Applied Physics Letters, 2021, 119, .	3.3	11
83	Enhancement of current to spin-current conversion and spin torque efficiencies in a synthetic antiferromagnetic layer based on a Pt/Ir/Pt spacer layer. Physical Review B, 2022, 105, .	3.2	11
84	Micromagnetic simulation of the temperature dependence of the switching energy barrier using string method assuming sidewall damages in perpendicular magnetized magnetic tunnel junctions. AIP Advances, 2020, 10, .	1.3	10
85	Electrical time-domain observation of magnetization switching induced by spin transfer in magnetic nanostructures (invited). Journal of Applied Physics, 2008, 103, 07A723.	2.5	9
86	Dependence of magnetic properties of MgO/CoFeB/Ta stacks on CoFeB and Ta thicknesses. Japanese Journal of Applied Physics, 2015, 54, 04DM04.	1.5	9
87	Origin of variation of shift field via annealing at 400°C in a perpendicular-anisotropy magnetic tunnel junction with [Co/Pt]-multilayers based synthetic ferrimagnetic reference layer. AIP Advances, 2017, 7, .	1.3	9
88	Current-driven magnetization reversal in exchange-biased spin-valve nanopillars. Journal of Applied Physics, 2005, 97, 114321.	2.5	8
89	Power-gated 32 bit microprocessor with a power controller circuit activated by deep-sleep-mode instruction achieving ultra-low power operation. Japanese Journal of Applied Physics, 2015, 54, 04DE08.	1.5	8
90	First Demonstration of 25-nm Quad Interface p-MTJ Device With Low Resistance-Area Product MgO and Ten Years Retention for High Reliable STT-MRAM. IEEE Transactions on Electron Devices, 2021, 68, 2680-2685.	3.0	8

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91	Time-Resolved Switching Characteristic in Magnetic Tunnel Junction with Spin Transfer Torque Write Scheme. Japanese Journal of Applied Physics, 2012, 51, 02BM02.	1.5	7
92	Electrical endurance of Co/Ni wire for magnetic domain wall motion device. Applied Physics Letters, 2013, 102, 222410.	3.3	7
93	Influence of heavy ion irradiation on perpendicular-anisotropy CoFeB-MgO magnetic tunnel junctions. , 2013, , .		7
94	Wide operational margin capability of 1 kbit spin-transfer-torque memory array chip with 1-PMOS and 1-bottom-pin-magnetic-tunnel-junction type cell. Japanese Journal of Applied Physics, 2014, 53, 04ED13.	1.5	7
95	Plasma process induced physical damages on multilayered magnetic films for magnetic domain wall motion. Japanese Journal of Applied Physics, 2014, 53, 03DF03.	1.5	7
96	Novel Method of Evaluating Accurate Thermal Stability for MTJs Using Thermal Disturbance and its Demonstration for Single-/Double-Interface p-MTJ. IEEE Transactions on Magnetics, 2018, 54, 1-5.	2.1	7
97	Effect of surface modification treatment of buffer layer on thermal tolerance of synthetic ferrimagnetic reference layer in perpendicular-anisotropy magnetic tunnel junctions. Journal of Applied Physics, 2019, 126, .	2.5	7
98	Fabrication of a 3000-6-input-LUTs embedded and block-level power-gated nonvolatile FPGA chip using p-MTJ-based logic-in-memory structure. , 2015, , .		6
99	Change in chemical bonding state by thermal treatment in MgO-based magnetic tunnel junction observed by angle-resolved hard X-ray photoelectron spectroscopy. Journal of Applied Physics, 2019, 125, .	2.5	6
100	Influence of Hard Mask Materials on the Magnetic Properties of Perpendicular MTJs With Double CoFeB/MgO Interface. IEEE Transactions on Magnetics, 2020, 56, 1-4.	2.1	6
101	Magnetic properties of Co film in Pt/Co/Cr2O3/Pt structure. AIP Advances, 2020, 10, .	1.3	6
102	Enhancement of magnetic coupling and magnetic anisotropy in MTJs with multiple CoFeB/MgO interfaces for high thermal stability. AIP Advances, 2021, 11, .	1.3	6
103	A 1-Mb STT-MRAM with zero-array standby power and 1.5-ns quick wake-up by 8-b fine-grained power gating. , 2013, , .		5
104	In-plane anisotropy of a nano-scaled magnetic tunnel junction with perpendicular magnetic easy axis. Japanese Journal of Applied Physics, 2015, 54, 04DM03.	1.5	5
105	Free- and reference-layer magnetization modes versus in-plane magnetic field in a magnetic tunnel junction with perpendicular magnetic easy axis. Physical Review B, 2016, 94, .	3.2	4
106	Fast neutron tolerance of the perpendicular-anisotropy CoFeB/MgO magnetic tunnel junctions with junction diameters between 46 and 64 nm. Japanese Journal of Applied Physics, 2017, 56, 0802B3.	1.5	4
107	STEM tomography study on structural features induced by MTJ processing. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	4
108	Transient Characteristic of Fabricated Magnetic Tunnel Junction (MTJ) Programmed with CMOS Circuit. IEICE Transactions on Electronics, 2010, E93-C, 602-607.	0.6	3

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109	Distribution of critical current density for magnetic domain wall motion. Journal of Applied Physics, 2014, 115, 17D508.	2.5	3
110	Power reduction by power gating in differential pair type spin-transfer-torque magnetic random access memories for low-power nonvolatile cache memories. Japanese Journal of Applied Physics, 2014, 53, 04ED04.	1.5	3
111	Effect of capping layer material on thermal tolerance of magnetic tunnel junctions with MgO/CoFeB-based free layer/MgO/capping layers. AIP Advances, 2019, 9, .	1.3	3
112	40 nm 1Tâ€“1MTJ 128 Mb STT-MRAM With Novel Averaged Reference Voltage Generator Based on Detailed Analysis of Scaled-Down Memory Cell Array Design. IEEE Transactions on Magnetics, 2021, 57, 1-9.	2.1	3
113	Perpendicular Magnetic Tunnel Junctions With Four Anti-Ferromagnetically Coupled Co/Pt Pinning Layers. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	3
114	2-Mb SPRAM design: bi-directional current write and parallelizing-direction current read based on spin-transfer torque switching. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 3929-3933.	1.8	2
115	Electric Field-Induced Magnetization Switching in CoFeB-MgOâ€“Static Magnetic Field Angle Dependence. IEEE Transactions on Magnetics, 2014, 50, 1-3.	2.1	2
116	Challenge of MTJ-based nonvolatile logic-in-memory architecture for ultra low-power and highly dependable VLSI computing. , 2015, , .		2
117	Effect of Magnetic Coupling Between Two CoFeB Layers on Thermal Stability in Perpendicular Magnetic Tunnel Junctions With MgO/CoFeB/Insertion Layer/CoFeB/MgO Free Layer. IEEE Transactions on Magnetics, 2022, 58, 1-6.	2.1	2
118	Fabrication and Evaluation of Magnetic Tunnel Junction with MgO Tunneling Barrier. Japanese Journal of Applied Physics, 2006, 45, 3228-3232.	1.5	1
119	Reduction of intrinsic critical current density under a magnetic field along the hard axis of a free layer in a magnetic tunnel junction. Physical Review B, 2011, 84, .	3.2	1
120	Material parameters and thermal stability of synthetic ferrimagnet free layers in magnetic tunnel junction nanopillars. Journal of Applied Physics, 2012, 112, 053922.	2.5	1
121	A two-transistor bootstrap type selective device for spin-transfer-torque magnetic tunnel junctions. Japanese Journal of Applied Physics, 2014, 53, 04ED03.	1.5	1
122	Beyond MRAM: Nonvolatile Logic-in-Memory VLSI. , 0, , 199-230.		1
123	A novel memory test system with an electromagnet for STT-MRAM testing. , 2019, , .		1
124	Influence of Iridium Sputtering Conditions on the Magnetic Properties of Co/Pt-Based Iridium-Synthetic Antiferromagnetic Coupling Reference Layer. IEEE Transactions on Magnetics, 2022, 58, 1-5.	2.1	1
125	Study of the DC Performance of Fabricated Magnetic Tunnel Junction Integrated on Back-End Metal Line of CMOS Circuits. IEICE Transactions on Electronics, 2010, E93-C, 608-613.	0.6	0
126	The Performance of Magnetic Tunnel Junction Integrated on the Back-End Metal Line of Complimentary Metalâ€“Oxideâ€“Semiconductor Circuits. Japanese Journal of Applied Physics, 2010, 49, 04DM06.	1.5	0

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127	Diffusion behaviors observed on the surface of CoFeB film after the natural oxidation and the annealing. , 2015, , .		0
128	High thermal tolerance synthetic ferrimagnetic reference layer with modified buffer layer by ion irradiation for perpendicular anisotropy magnetic tunnel junctions.. , 2018, , .		0
129	Structural Analysis of CoFeB/MgO-Based Perpendicular MTJs With Junction Size of 20 nm by STEM Tomography. IEEE Transactions on Magnetics, 2021, 57, 1-7.	2.1	0